

## ULTRAFAST SOFT RECOVERY RECTIFIER DIODE

### PRODUCT APPLICATIONS

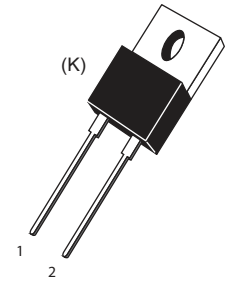
- Anti-Parallel Diode
  - Switchmode Power Supply
  - Inverters
- Free Wheeling Diode
  - Motor Controllers
  - Converters
  - Inverters
- Snubber Diode
- PFC

### PRODUCT FEATURES

- Ultrafast Recovery Times
- Soft Recovery Characteristics
- Popular TO-220 Package
- Low Forward Voltage
- Low Leakage Current
- Avalanche Energy Rated

### PRODUCT BENEFITS

- Low Losses
- Low Noise Switching
- Cooler Operation
- Higher Reliability Systems
- Increased System Power Density



1 - Cathode  
 2 - Anode  
 Back of Case - Cathode

### MAXIMUM RATINGS

All Ratings:  $T_C = 25^\circ\text{C}$  unless otherwise specified.

Symbol	Characteristic / Test Conditions	APT30DQ100K(G)	UNIT
$V_R$	Maximum D.C. Reverse Voltage	1000	Volts
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage		
$V_{RWM}$	Maximum Working Peak Reverse Voltage		
$I_{F(AV)}$	Maximum Average Forward Current ( $T_C = 102^\circ\text{C}$ , Duty Cycle = 0.5)	30	Amps
$I_{F(RMS)}$	RMS Forward Current (Square wave, 50% duty)	43	
$I_{FSM}$	Non-Repetitive Forward Surge Current ( $T_J = 45^\circ\text{C}$ , 8.3ms)	150	
$E_{AVL}$	Avalanche Energy (1A, 40mH)	20	mJ
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to 175	°C
$T_L$	Lead Temperature for 10 Sec.	300	

### STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT	
$V_F$	Forward Voltage		$I_F = 30\text{A}$	2.5	3.0	Volts
			$I_F = 60\text{A}$	3.06		
			$I_F = 30\text{A}, T_J = 125^\circ\text{C}$	1.92		
$I_{RM}$	Maximum Reverse Leakage Current		$V_R = 1000\text{V}$		100	μA
			$V_R = 1000\text{V}, T_J = 125^\circ\text{C}$		500	
$C_T$	Junction Capacitance, $V_R = 200\text{V}$		26		pF	

DYNAMIC CHARACTERISTICS

APT30DQ100K(G)

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
$t_{rr}$	Reverse Recovery Time	$I_F = 1A, di_F/dt = -100A/\mu s, V_R = 30V, T_J = 25^\circ C$	-	24		ns
$t_{rr}$	Reverse Recovery Time	$I_F = 30A, di_F/dt = -200A/\mu s, V_R = 667V, T_C = 25^\circ C$	-	295		
$Q_{rr}$	Reverse Recovery Charge		-	440		nC
$I_{RRM}$	Maximum Reverse Recovery Current		-	4	-	Amps
$t_{rr}$	Reverse Recovery Time	$I_F = 30A, di_F/dt = -200A/\mu s, V_R = 667V, T_C = 125^\circ C$	-	330		ns
$Q_{rr}$	Reverse Recovery Charge		-	1550		nC
$I_{RRM}$	Maximum Reverse Recovery Current		-	8	-	Amps
$t_{rr}$	Reverse Recovery Time	$I_F = 30A, di_F/dt = -1000A/\mu s, V_R = 667V, T_C = 125^\circ C$	-	150		ns
$Q_{rr}$	Reverse Recovery Charge		-	2250		nC
$I_{RRM}$	Maximum Reverse Recovery Current		-	25		Amps

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-Case Thermal Resistance			.80	$^\circ C/W$
$W_T$	Package Weight		0.07		oz
			1.9		g
Torque	Maximum Mounting Torque			10	lb•in
				1.1	N•m

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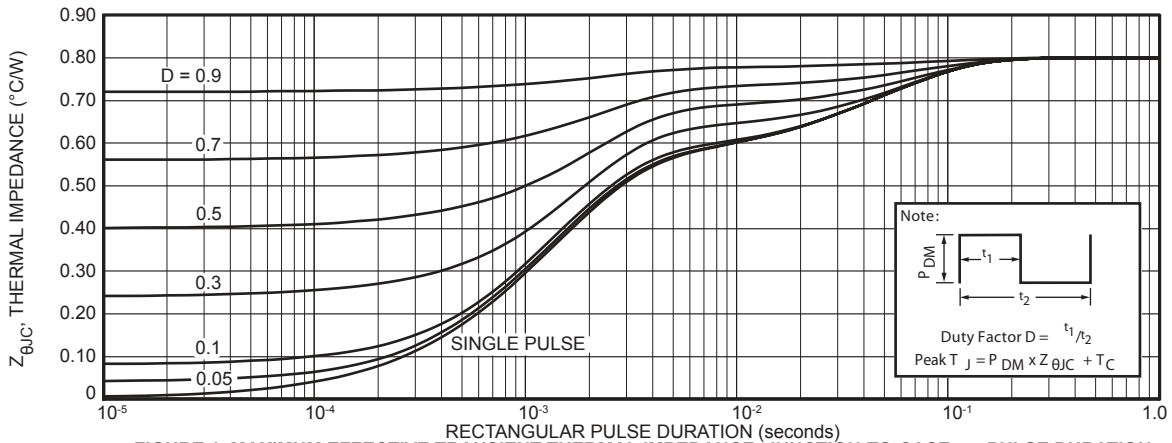


FIGURE 1. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

TYPICAL PERFORMANCE CURVES

APT30DQ100K(G)

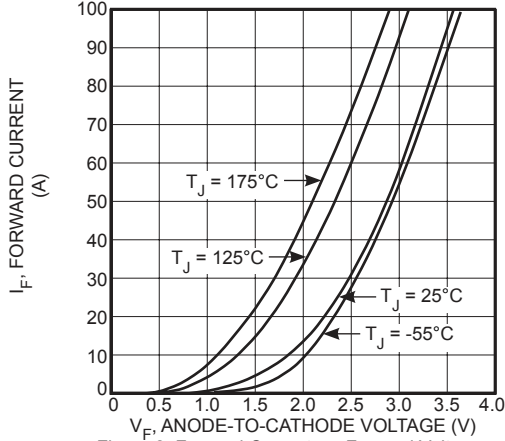


Figure 2. Forward Current vs. Forward Voltage

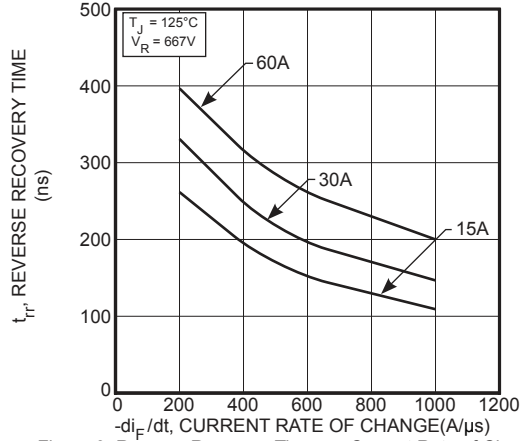


Figure 3. Reverse Recovery Time vs. Current Rate of Change

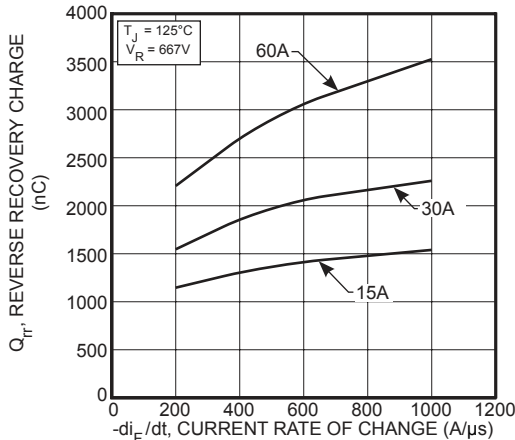


Figure 4. Reverse Recovery Charge vs. Current Rate of Change

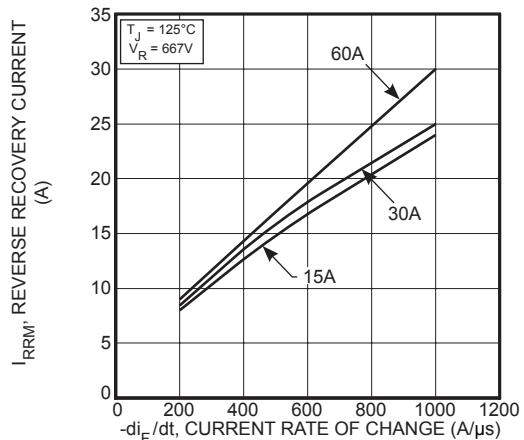


Figure 5. Reverse Recovery Current vs. Current Rate of Change

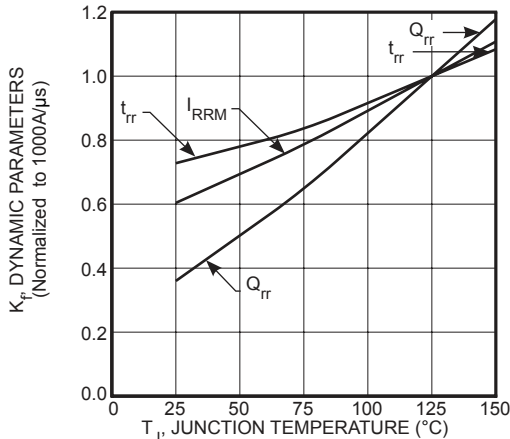


Figure 6. Dynamic Parameters vs. Junction Temperature

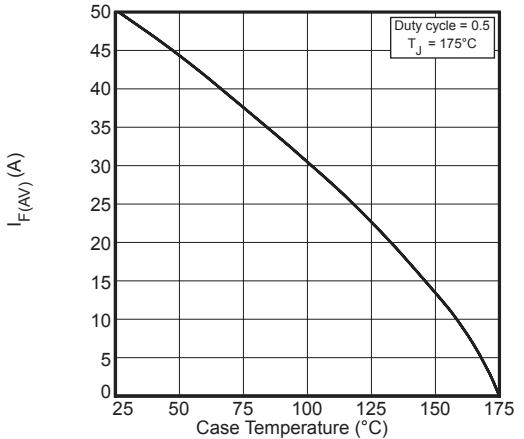


Figure 7. Maximum Average Forward Current vs. Case Temperature

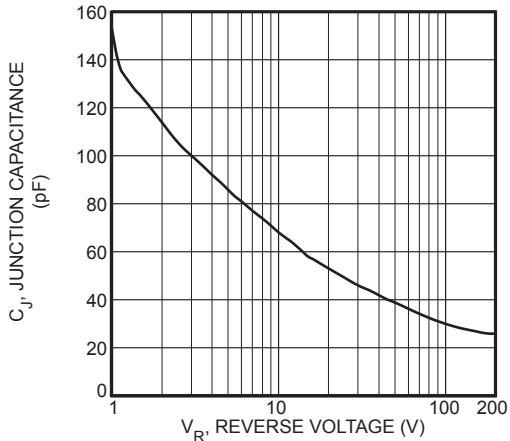


Figure 8. Junction Capacitance vs. Reverse Voltage

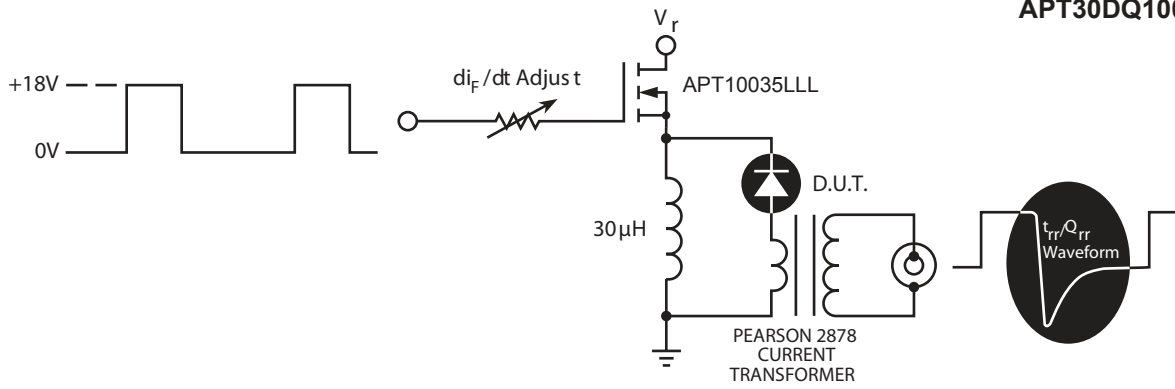


Figure 9. Diode Test Circuit

- 1  $I_F$  - Forward Conduction Current
- 2  $di_F/dt$  - Rate of Diode Current Change Through Zero Crossing.
- 3  $I_{RRM}$  - Maximum Reverse Recovery Current
- 4  $t_{rr}$  - Reverse Recovery Time measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through  $I_{RRM}$  and  $0.25 I_{RRM}$  passes through zero.
- 5  $Q_{rr}$  - Area Under the Curve Defined by  $I_{RRM}$  and  $t_{rr}$ .

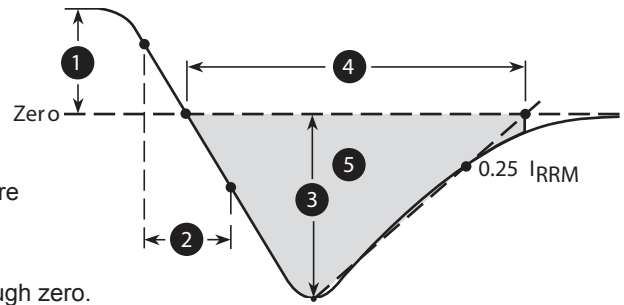
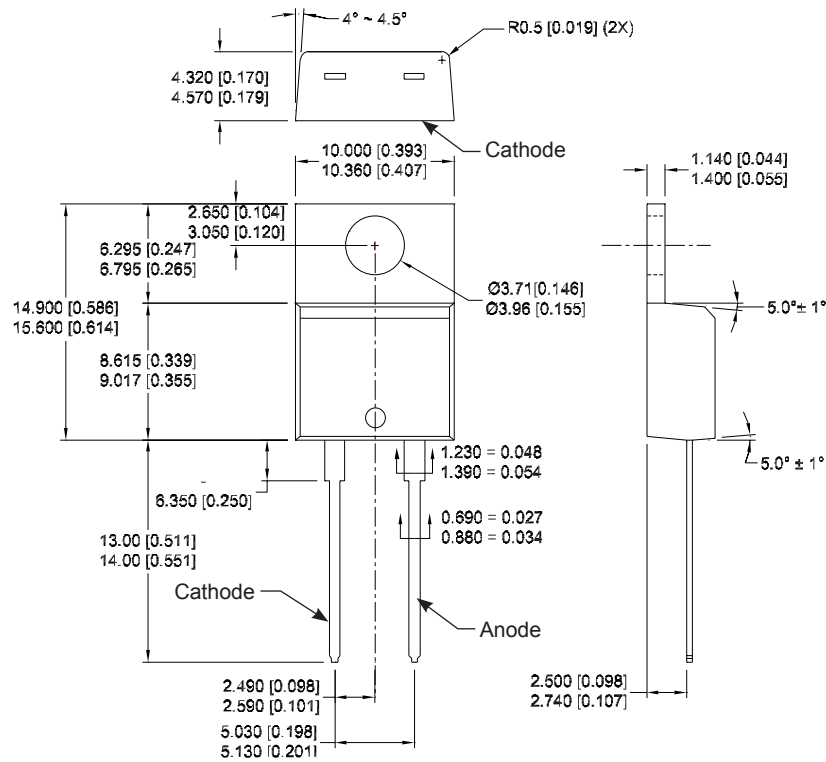


Figure 10. Diode Reverse Recovery Waveform Definition

**TO-220 (K) Package Outline**

e3 100% Sn



Dimensions in millimeters and [inches]

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